DATA SHEET

NEC

PHOTOCOUPLER

PS2703-1,PS2703-2,PS2703-4

HIGH ISOLATION VOLTAGE HIGH COLLECTOR TO EMITTER VOLTAGE SOP MULTI PHOTOCOUPLER

–NEPOC™ Series–

DESCRIPTION

The PS2703-1, PS2703-2, PS2703-4, are optically coupled isolators containing a GaAs light emitting diode and an NPN silicon phototransistor.

Each is mounted in a plastic SOP (Small Out-line Package) for high density applications.

This package has shield effect to cut off ambient light.

FEATURES

- High isolation voltage (BV: 3 750 Vr.m.s.)
- SOP (Small Out-line Package)
- Each isolated channels per package
- High collector to emitter voltage (V_{CEO} = 120 V)
- High-speed switching (t_r, t_f = 10 μs)
- Taping product number (Only-1 type) (PS2703-1-E3, -E4, -F3, -F4)
- UL approved (File No. E72422 (S))
- VDE0884 approved (Option)

★ APPLICATIONS

- Hibrid IC
- Measuring instruments
- Power supply
- Programmable logic controllers

ORDERING INFORMATION

Part Number	Package	Safety Standard Approval
PS2703-1	4-pin SOP	Standard specification products
PS2703-2	8-pin SOP	• UL approved
PS2703-4	16-pin SOP	
PS2703-1-V	4-pin SOP	VDE0884 specification products (Option)
PS2703-2-V	8-pin SOP	• VDE approved
PS2703-4-V	16-pin SOP	

The information in this document is subject to change without notice.

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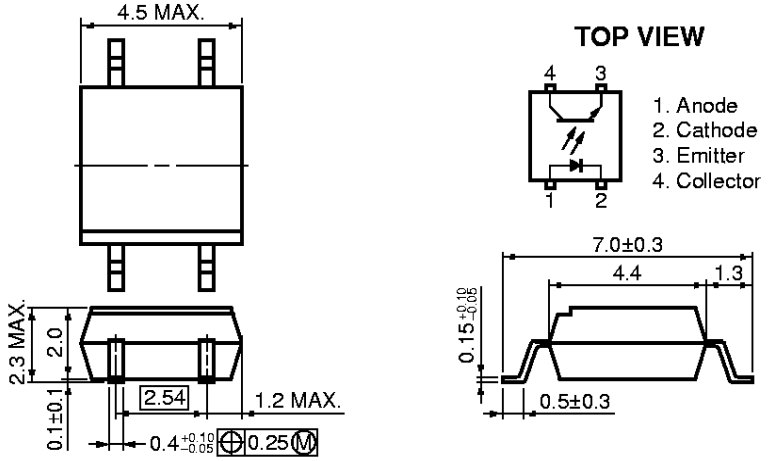
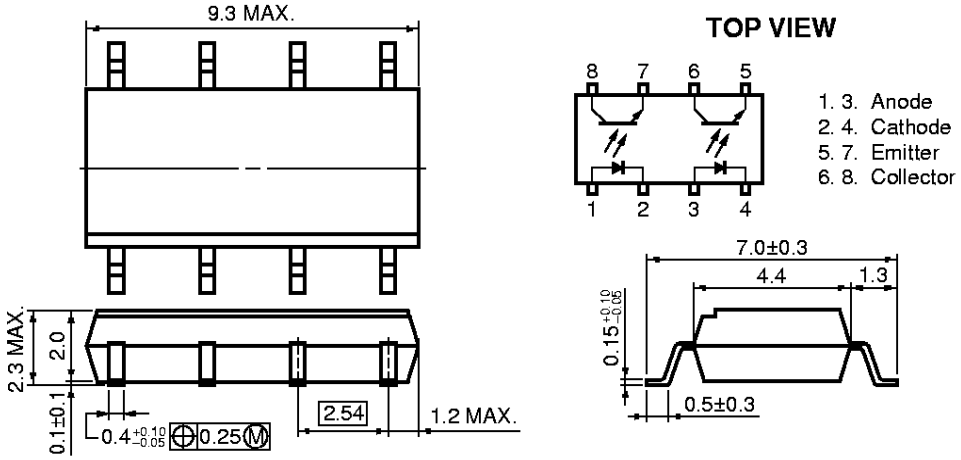
The mark ★ shows major revised points.

PACKAGE DIMENSIONS (in millimeters)

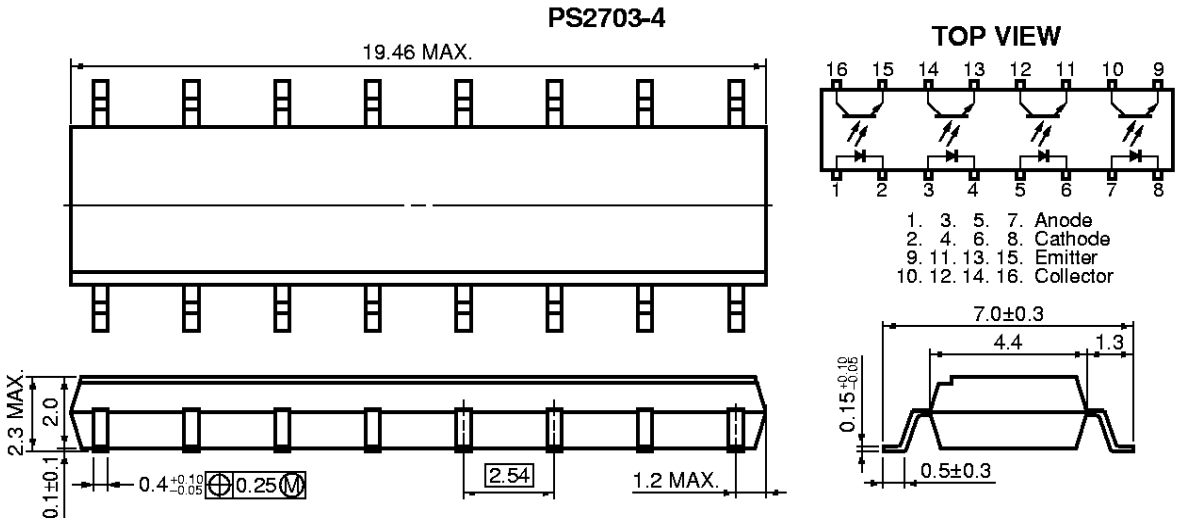
PS2703-1



PS2703-2



PS2703-4



ABSOLUTE MAXIMUM RATINGS (T_A = 25 °C, unless otherwise specified)

Parameter		Symbol	Ratings		Unit
			PS2703-1	PS2703-2, PS2703-4	
Diode	Forward Current (DC)	I_F	50		mA
	Reverse Voltage	V_R	6.0		V
	Power Dissipation Derating	ΔP_D/°C	0.8		mW/°C
	Power Dissipation	P_D	80		mW/ch
	Peak Forward Current*1	I_{FP}	1		A
Transistor	Collector to Emitter Voltage	V_{CEO}	120		V
	Emitter to Collector Voltage	V_{ECO}	6		V
	Collector Current	I_C	30		mA/ch
	Power Dissipation Derating	ΔP_C/°C	1.5	1.2	mW/°C
	Power Dissipation	P_C	150	120	mW/ch
Isolation Voltage*2		BV	3 750		Vr.m.s.
Operating Ambient Temperature		T_A	–55 to +100		°C
Storage Temperature		T_{stg}	–55 to +150		°C

*1 PW = 100 μs, Duty Cycle = 1 %

*2 AC voltage for 1 minute at T_A = 25 °C, RH = 60 % between input and output

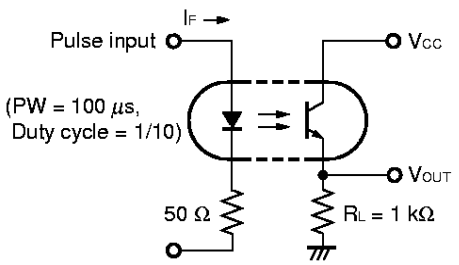
ELECTRICAL CHARACTERISTICS (T_A = 25 °C)

Parameter		Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Diode	Forward Voltage	V_F	I_F = 5 mA		1.1	1.4	V
	Reverse Current	I_R	V_R = 5 V			5	μA
	Terminal Capacitance	C_t	V = 0 V, f = 1 MHz		30		pF
Transistor	Collector to Emitter Current	I_{CEO}	I_F = 0 mA, V_{CE} = 120 V			100	nA
Coupled	Current Transfer Ratio*1	CTR	I_F = 5 mA, V_{CE} = 5 V	50	150	400	%
			I_F = 1 mA, V_{CE} = 5 V	10	80		
	Collector Saturation Voltage	$V_{CE\ (sat)}$	I_F = 10 mA, I_C = 2 mA			0.3	V
	Isolation Resistance	R_{I-O}	V_{I-O} = 1 kV_{DC}	10^{11}			Ω
	Isolation Capacitance	C_{I-O}	V = 0 V, f = 1 MHz		0.4		pF
	Rise Time *2	t_r	V_{CC} = 5 V, I_C = 2 mA, R_L = 1 kΩ		10		μs
	Fall Time *2	t_f					

*1 CTR rank (only PS2703-1)

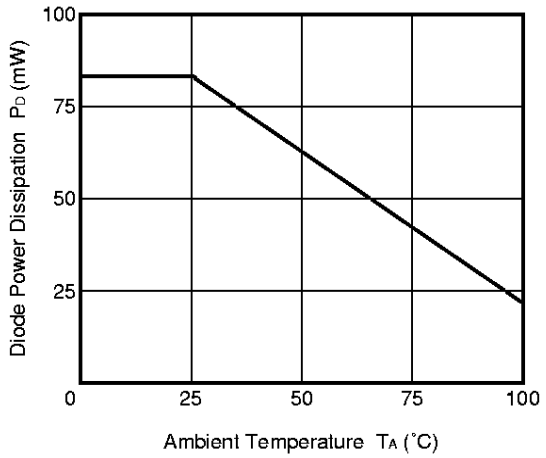
CTR rank	CTR (%)	Conditions
K	200 to 400	I_F = 5 mA, V_{CE} = 5 V
	80 to	I_F = 1 mA, V_{CE} = 5 V
L	100 to 300	I_F = 5 mA, V_{CE} = 5 V
	25 to	I_F = 1 mA, V_{CE} = 5 V
M	50 to 150	I_F = 5 mA, V_{CE} = 5 V
	10 to	I_F = 1 mA, V_{CE} = 5 V

*2 Test circuit for switching time

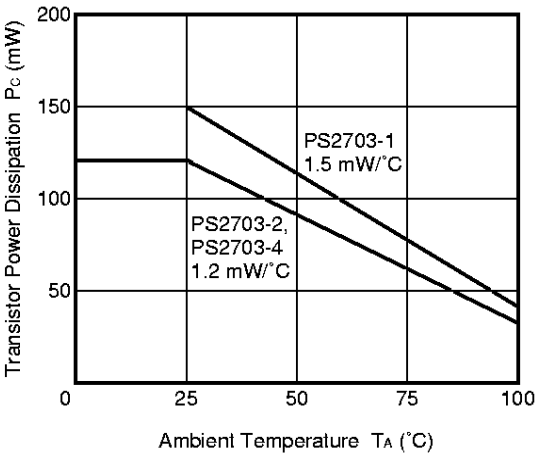


TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise specified)

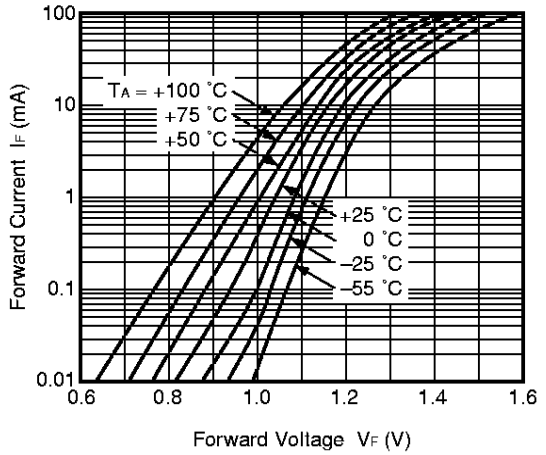
DIODE POWER DISSIPATION vs. AMBIENT TEMPERATURE



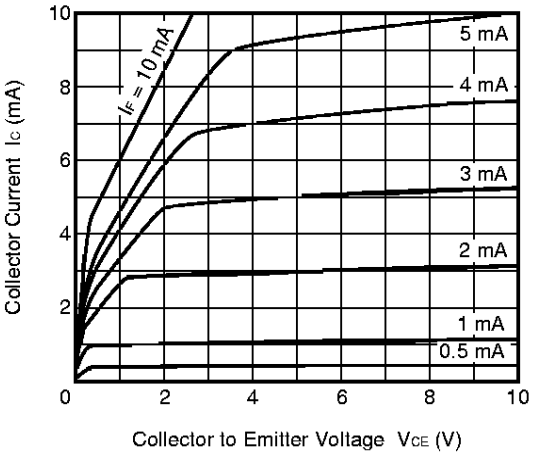
TRANSISTOR POWER DISSIPATION vs. AMBIENT TEMPERATURE



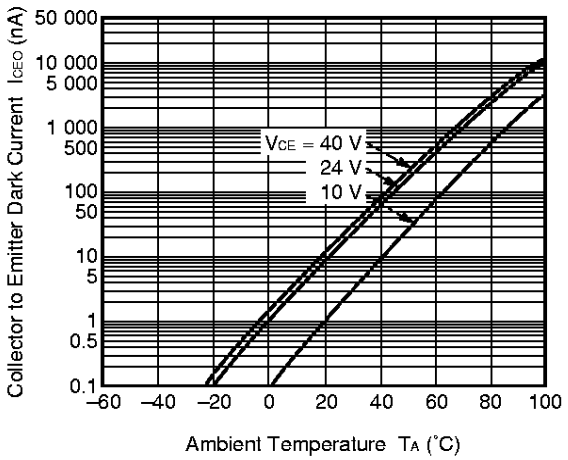
FORWARD CURRENT vs. FORWARD VOLTAGE



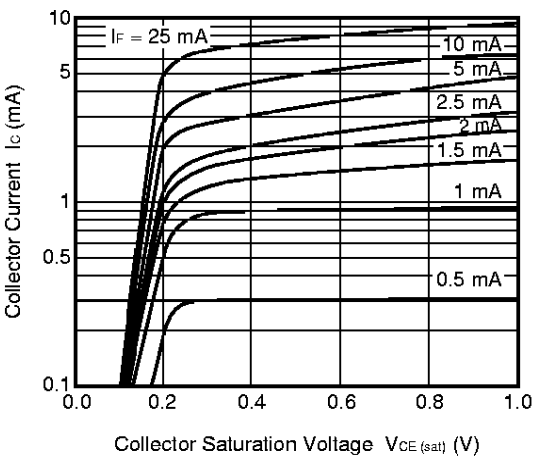
COLLECTOR CURRENT vs. COLLECTOR TO EMITTER VOLTAGE



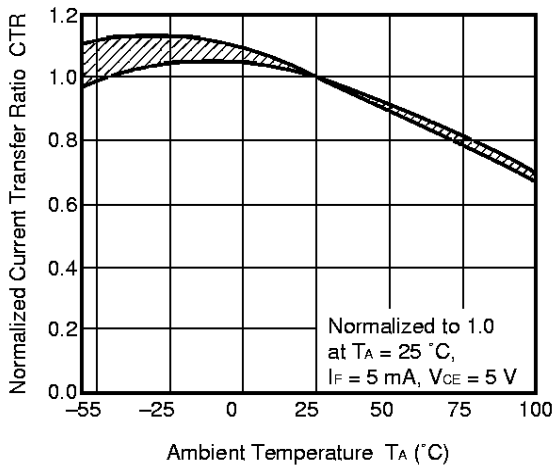
COLLECTOR TO EMITTER DARK CURRENT vs. AMBIENT TEMPERATURE



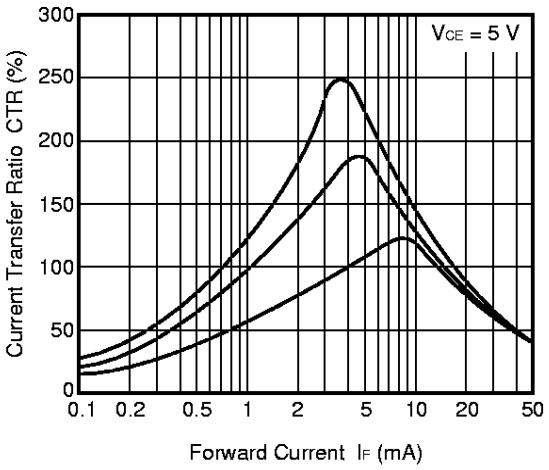
COLLECTOR CURRENT vs. COLLECTOR SATURATION VOLTAGE



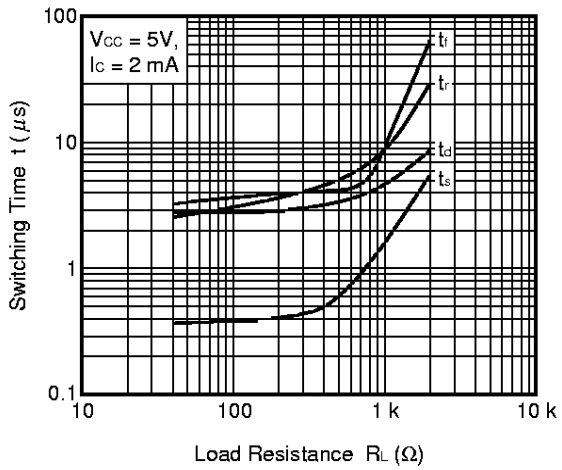
NORMALIZED CURRENT TRANSFER RATIO vs. AMBIENT TEMPERATURE



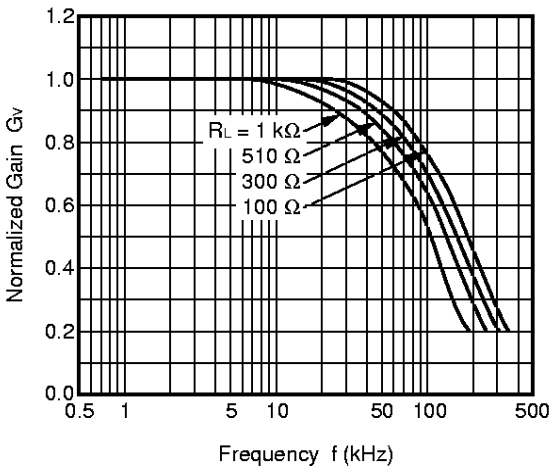
CURRENT TRANSFER RATIO vs. FORWARD CURRENT



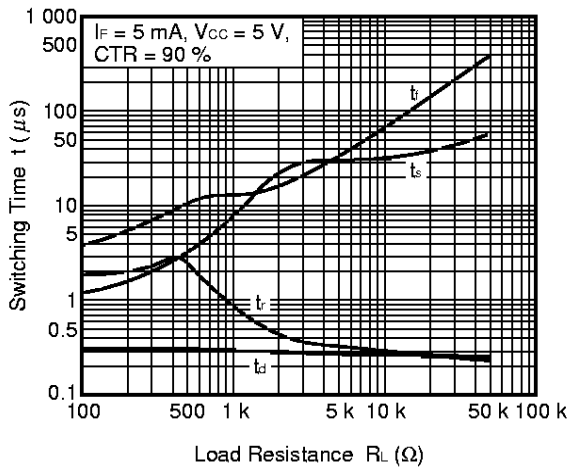
SWITCHING TIME vs. LOAD RESISTANCE



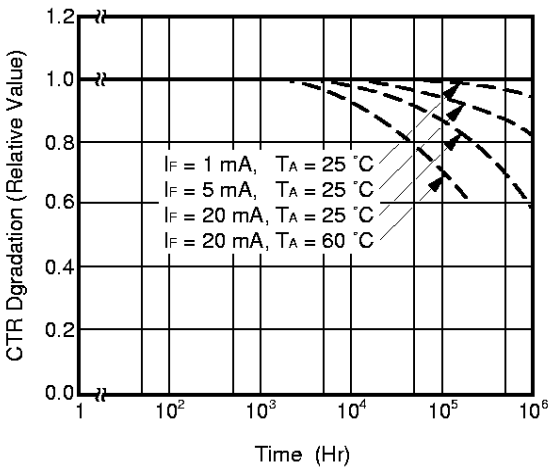
FREQUENCY RESPONSE



SWITCHING TIME vs. LOAD RESISTANCE

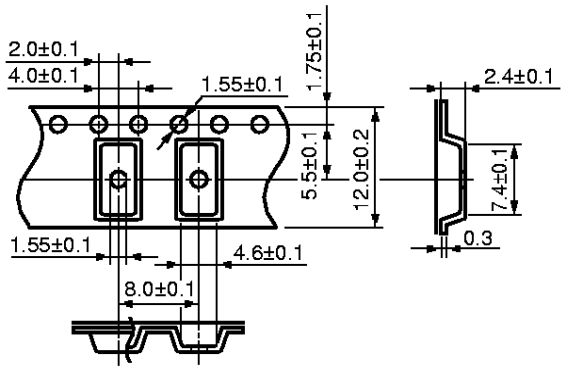


LONG TIME CTR DEGRADATION

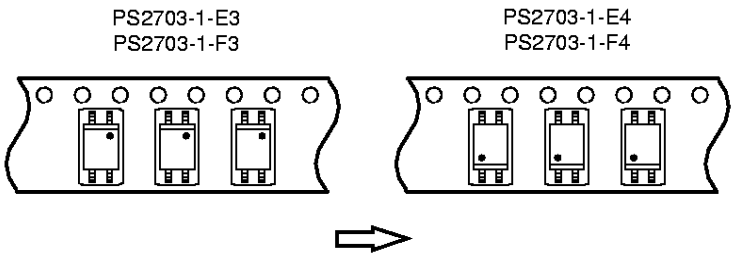


★ **TAPING SPECIFICATIONS (in millimeters)**

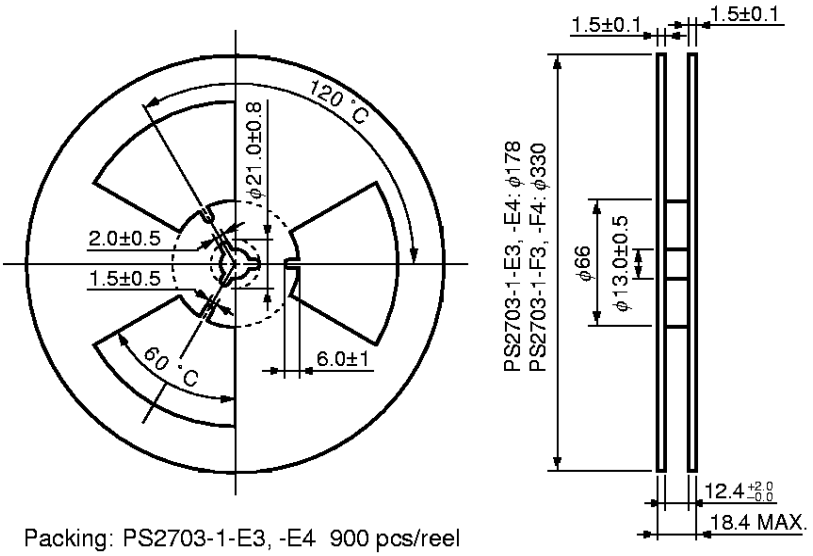
Outline and Dimensions (Tape)



Taping Direction



Outline and Dimensions (Reel)



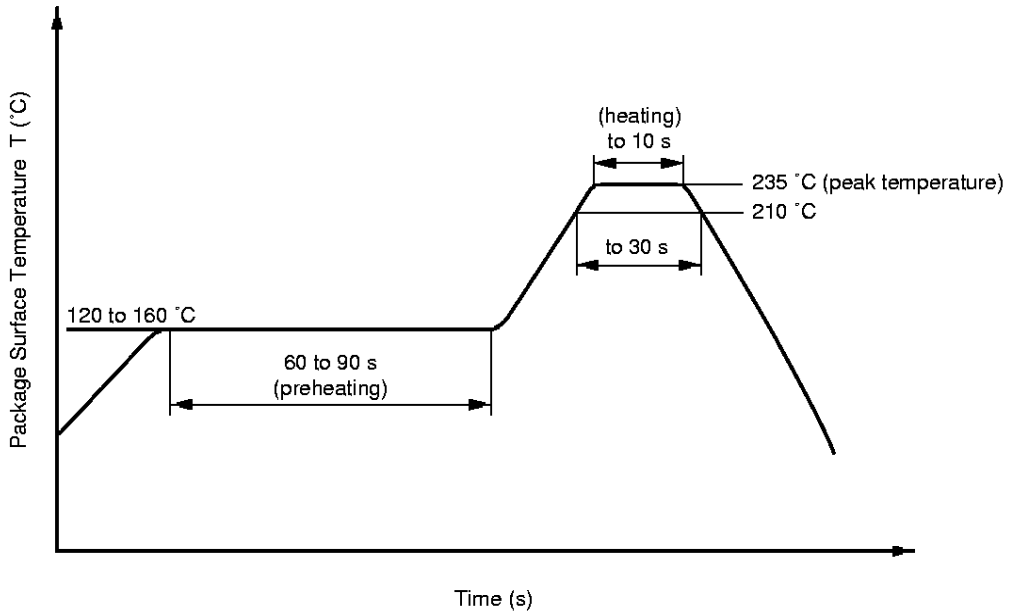
Packing: PS2703-1-E3, -E4 900 pcs/reel
PS2703-1-F3, -F4 3 500 pcs/reel

RECOMMENDED SOLDERING CONDITIONS

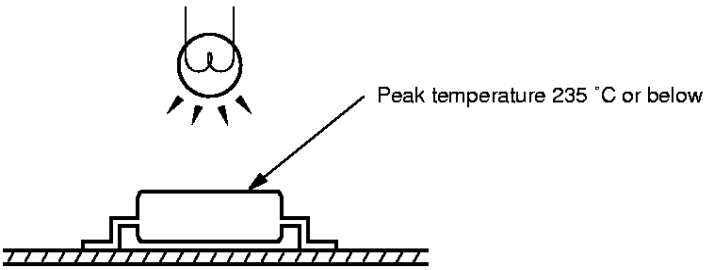
(1) Infrared reflow soldering

• Peak reflow temperature	235 °C (package surface temperature)
• Time of temperature higher than 210 °C	30 seconds or less
• Number of reflows	Three
• Flux	Rosin flux containing small amount of chlorine (The flux with a maximum chlorine content of 0.2 Wt % is recommended.)

Recommended Temperature Profile of Infrared Reflow



Caution Please avoid to removed the residual flux by water after the first reflow processes.



(2) Dip soldering

• Temperature	260 °C or below (molten solder temperature)
• Time	10 seconds or less
• Number of times	One
• Flux	Rosin flux containing small amount of chlorine (The flux with a maximum chlorine content of 0.2 Wt % is recommended.)

SPECIFICATION OF VDE MARKS LICENSE DOCUMENT (VDE0884)

Parameter	Symbol	Speck	Unit
Application classification (DIN VDE 0109)			
for rated line voltages ≤ 300 Vr.m.s.		IV	
for rated line voltages ≤ 600 Vr.m.s.		III	
Climatic test class (DIN IEC 68 Teil 1/09.80)		55/100/21	
Dielectric strength maximum operating isolation voltage.			
Test voltage (partial discharge test procedure a for type test and random test)	U_{IORM}	710	V_{peak}
U_{pr} = 1.2 × U_{IORM}, P_d < 5 pC	U_{pr}	850	V_{peak}
Test voltage (partial discharge test procedure b for random test) U_{pr} = 1.6 × U_{IORM}, P_d < 5 pC	U_{pr}	1 140	V_{peak}
Highest permissible overvoltage	U_{TR}	6 000	V_{peak}
Degree of pollution (DIN VDE 0109)		2	
Clearance distance		> 5	mm
Creepage distance		> 5	mm
Comparative tracking index (DIN IEC 112/VDE 0303 part 1)	CTI	175	
Material group (DIN VDE 0109)		IIIa	
Storage temperature range	T_{stg}	–55 to +150	°C
Operating temperature range	T_A	–55 to +100	°C
Isolation resistance, minimum value			
V_{IO} = 500 V dc at T_A = 25 °C	Ris MIN.	10^{12}	Ω
V_{IO} = 500 V dc at T_A MAX. at least 100 °C	Ris MIN.	10^{11}	Ω
Safety maximum ratings (maximum permissible in case of fault, see thermal derating curve)			
Package temperature	Tsi	150	°C
Current (input current I_F, Psi = 0)	Isi	200	mA
Power (output or total power dissipation)	Psi	300	mW
Isolation resistance			
V_{IO} = 500 V dc at T_A = 175 °C (Tsi)	Ris MIN.	10^9	Ω

[MEMO]

[MEMO]

CAUTION

Within this device there exists GaAs (Gallium Arsenide) material which is a harmful substance if ingested. Please do not under any circumstances break the hermetic seal.

NEPOC is a trademark of NEC Corporation.

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